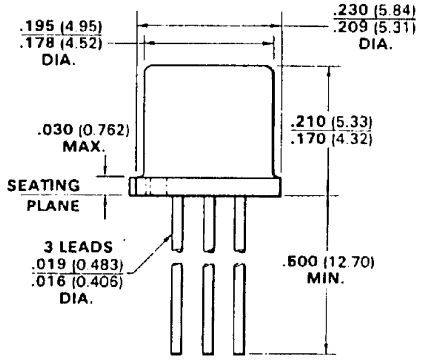
GERMANIUM TUNNEL DIODE

DESCRIPTION:

The **1N2927** is Designed for Switching Applications in Industrial and Miitary Applications.

PACKAGE STYLE TO-18



MAXIMUM RATINGS

I_F	500 µA
T_J	-65 ^{O}C to +150 ^{O}C
T_{STG}	-65 ^{O}C to +200 ^{O}C
T_{SOLD}	10 S/250 ^{O}C

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_P		90		110	µA
I_V				35	µA
V_P				75	mV
V_V				475	mV
V_F	I_F = 110 µA	600		1000	mV
I_R				1.0	mA

ADVANCED SEMICONDUCTOR, INC.

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Specifications are subject to change without notice.